PHPT60603PY

60 V, 3 A PNP high power bipolar transistor

13 January 2014

Product data sheet

1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT60603NY.

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-60	V
I _C	collector current		-	-	-3	Α
I _{CM}	peak collector current	$t_p \le 1 \text{ ms; pulsed}$	-	-	-8	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	80	120	mΩ



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	Е	emitter		в—
3	Е	emitter	[d	1.4
4	В	base	وققق	sym132
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package	e					
	Name	Description	Version				
PHPT60603PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT60603PY	0603PAB

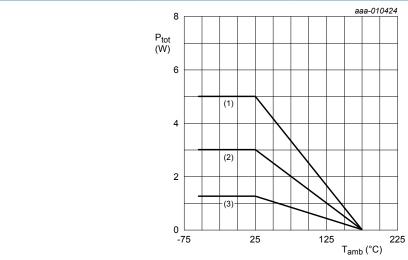
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-60	V
V_{CEO}	collector-emitter voltage	open base		-	-60	V
V_{EBO}	emitter-base voltage	open collector		-	-8	V
I _C	collector current			-	-3	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; pulsed		-	-8	Α
I _B	base current			-	-0.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[3]	-	5	W
			[4]	-	25	W
T _j	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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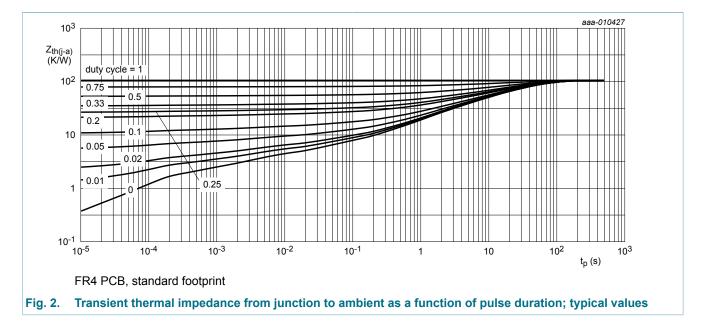
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9. Thermal characteristics

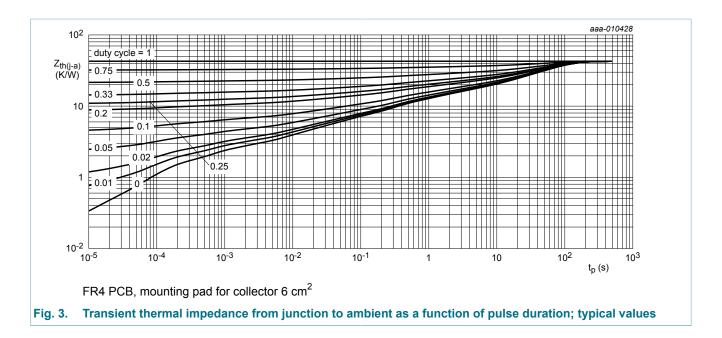
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resista from junction t ambient	thermal resistance		[1]	-	-	115	K/W
			[2]	-	-	50	K/W
	ambient		<u>[3]</u>	-	-	30	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	6	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



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10. Characteristics

Table 7. Characteristics

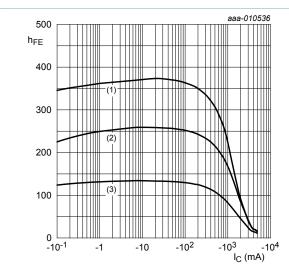
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V_{CB} = -48 V; I_E = 0 A; T_{amb} = 25 °C	-	-	-100	nA
	current	$V_{CB} = -48 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	$V_{CE} = -48 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = -8 V; I_{C} = 0 A; T_{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -500 mA; T_{amb} = 25 °C	150	250	-	
		V_{CE} = -2 V; I_{C} = -1 A; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C; pulsed	150	225	-	
		V_{CE} = -2 V; I_{C} = -2 A; t_{p} ≤ 300 µs; δ ≤ 0.02 ; T_{amb} = 25 °C; pulsed	80	130	-	
		V_{CE} = -2 V; I_{C} = -3 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	35	75	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -1 A; I_B = -50 mA; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-100	-225	mV
	I_C = -3 A; I_B = -300 mA; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C; pulsed	-	-240	-360	mV	
R _{CEsat} collector-emitter saturation resistance		I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	100	225	mΩ
		I_{C} = -3 A; I_{B} = -300 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	80	120	mΩ
V_{BEsat}	base-emitter saturation voltage	I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-0.89	-1	V
		I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-1.02	-1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -0.1 A; T_{amb} = 25 °C	-	-0.83	-0.9	V
t _d	delay time	V_{CC} = -12.5 V; I_C = -1 A; I_{Bon} = -50 mA;	-	15	-	ns
t _r	rise time	I_{Boff} = 50 mA; T_{amb} = 25 °C	-	85	-	ns
t _{on}	turn-on time		-	100	-	ns
t _s	storage time		-	350	-	ns
t _f	fall time		-	110	-	ns
t _{off}	turn-off time		-	460	-	ns
f _T	transition frequency	V _{CE} = -10 V; I _C = -100 mA; f = 100 MHz; T _{amb} = 25 °C	-	110	-	MHz

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$	-	60	-	pF
		f = 1 MHz; T _{amb} = 25 °C				



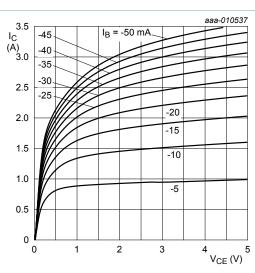


(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

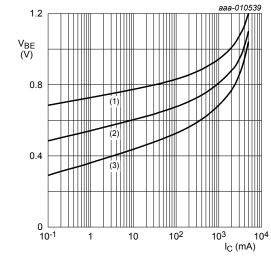
(3)
$$T_{amb} = -55$$
 °C

Fig. 4. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



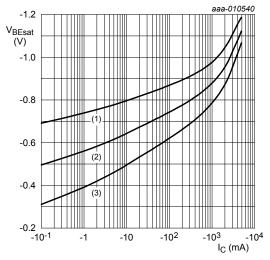
 $V_{CE} = -2 V$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 20$$

(1)
$$T_{amb} = -55$$
 °C

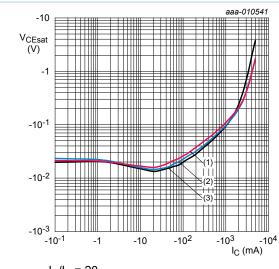
(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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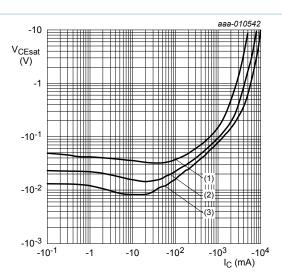
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55$$
 °C

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



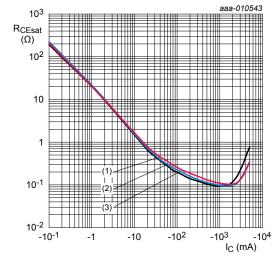
$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 50$$

(2)
$$I_C/I_B = 20$$

(3)
$$I_C/I_B = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



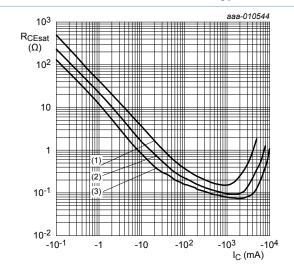
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55$$
 °C

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 50$$

(2)
$$I_C/I_B = 20$$

(3)
$$I_C/I_B = 10$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

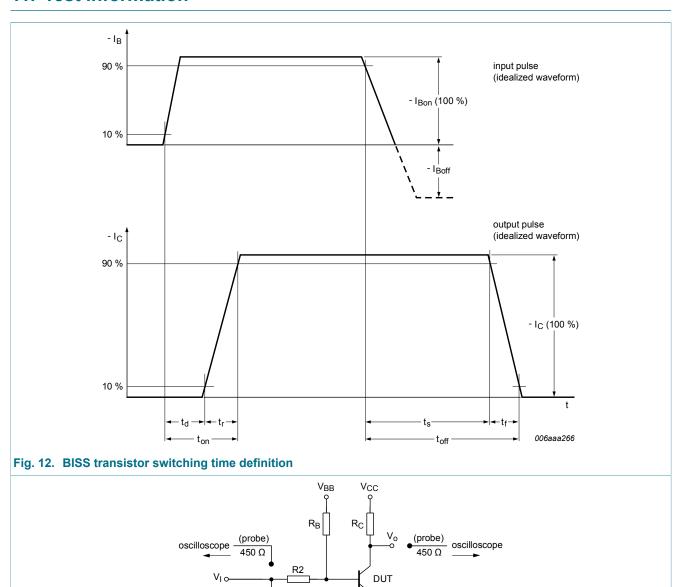


Fig. 13. Test circuit for switching times

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

mgd624

12. Package outline

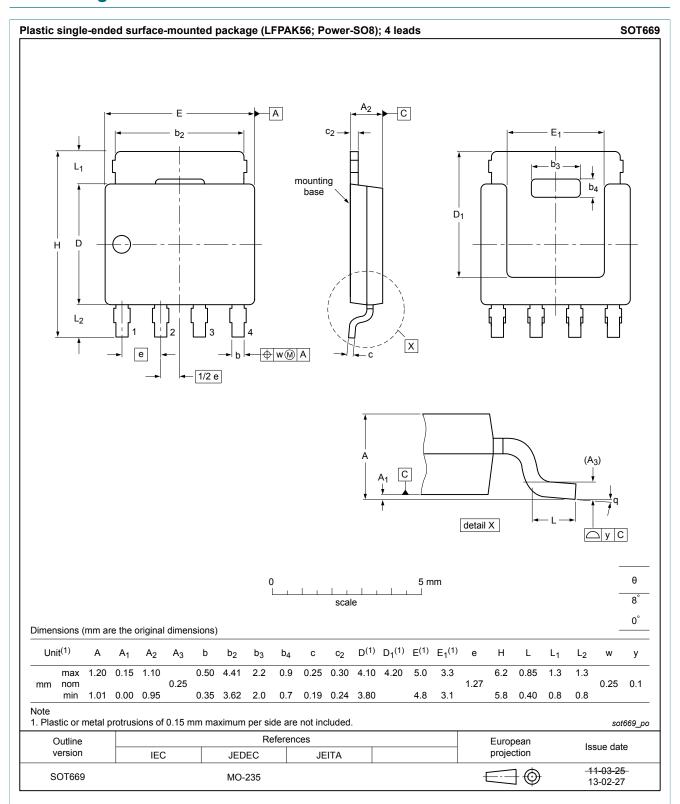


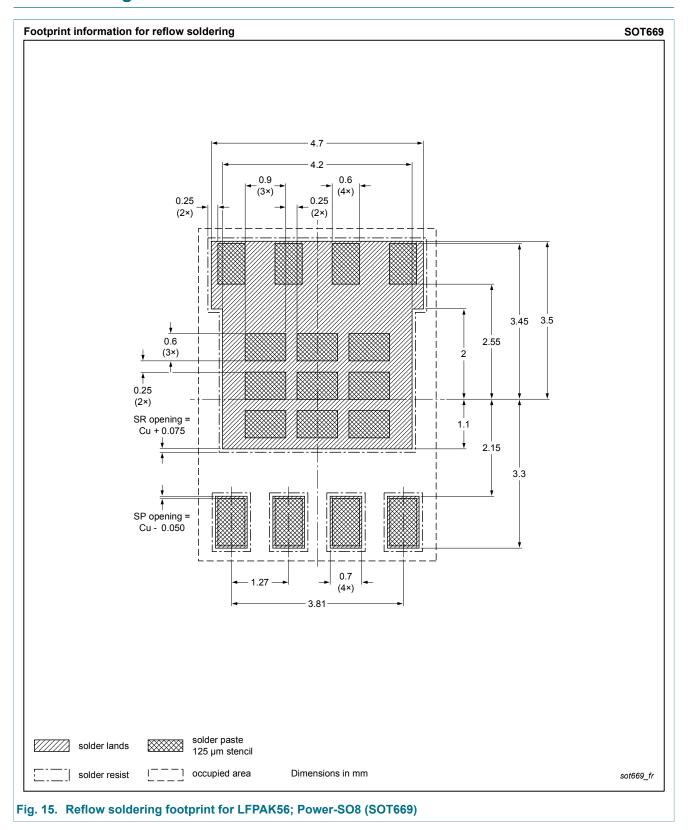
Fig. 14. Package outline LFPAK56; Power-SO8 (SOT669)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT60603PY v.1	20140113	Product data sheet	-	-

15. Legal information

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Document status [1][2]	Product status [3]	Definition
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